

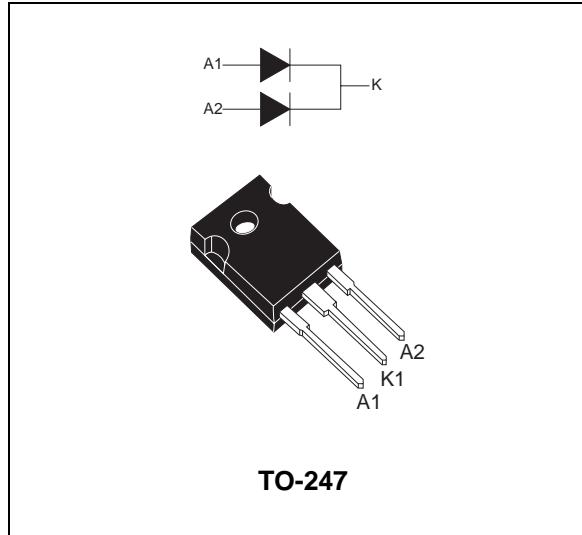
HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	2 x 15 A
V_{RRM}	100 V
T_{j(max)}	175 °C
V_{F(max)}	0.67 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW LEAKAGE CURRENT
- GOOD TRADE OFF BETWEEN LEAKAGE CURRENT AND FORWARD VOLTAGE DROP
- LOW THERMAL RESISTANCE
- AVALANCHE RATED



DESCRIPTION

Dual center tap Schottky rectifier suited for Switch Mode Power Supplies and high frequency DC to DC converters. Packaged in TO-247, this device is intended for use in high frequency inverters.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit		
V _{RRM}	Repetitive peak reverse voltage			100	V		
I _{F(RMS)}	RMS forward current			30	A		
I _{F(AV)}	Average forward current	T _c = 155°C δ = 0.5	Per diode Per device	15 30	A		
I _{FSM}	Surge non repetitive forward current	tp = 10 ms sinusoidal		250	A		
I _{RRM}	Repetitive peak reverse current	tp = 2 μs square F = 1kHz		1	A		
I _{RSM}	Non repetitive peak reverse current	tp = 100 μs square		3	A		
T _{stg}	Storage temperature range			- 65 to + 175	°C		
T _j	Maximum operating junction temperature *			175	°C		
dV/dt	Critical rate of rise of reverse voltage			10000	V/μs		

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th}(j-a)}$ thermal runaway condition for a diode on its own heatsink

STPS30H100CW

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode Total	1.6 0.9
		Coupling	0.1
$R_{th(c)}$			

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R *	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			5	μA
		$T_j = 125^\circ\text{C}$			2	6	mA
V_F **	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 15 \text{ A}$			0.80	V
		$T_j = 125^\circ\text{C}$	$I_F = 15 \text{ A}$		0.64	0.67	
		$T_j = 25^\circ\text{C}$	$I_F = 30 \text{ A}$			0.93	
		$T_j = 125^\circ\text{C}$	$I_F = 30 \text{ A}$		0.74	0.80	

Pulse test : * $t_p = 5 \text{ ms}, \delta < 2\%$
** $t_p = 380 \mu\text{s}, \delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.54 \times I_{F(AV)} + 0.0086 \times I_{F^2(RMS)}$$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

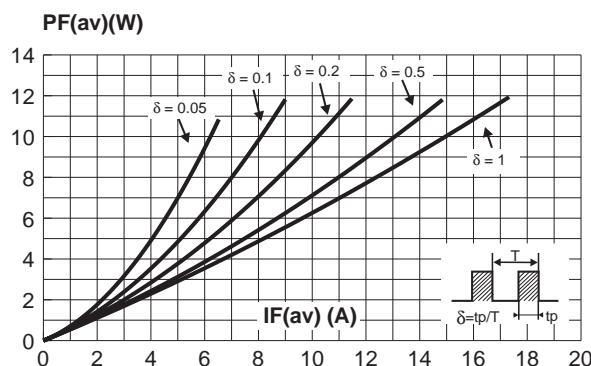


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$, per diode).

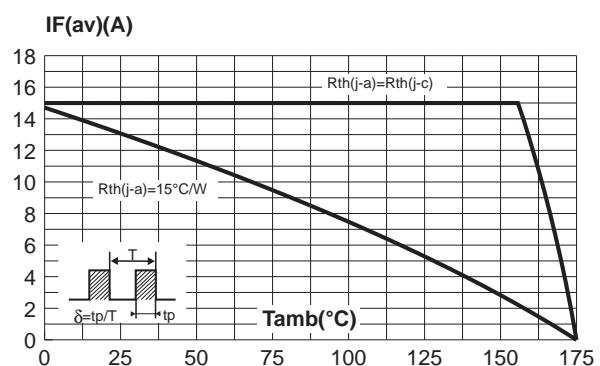


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

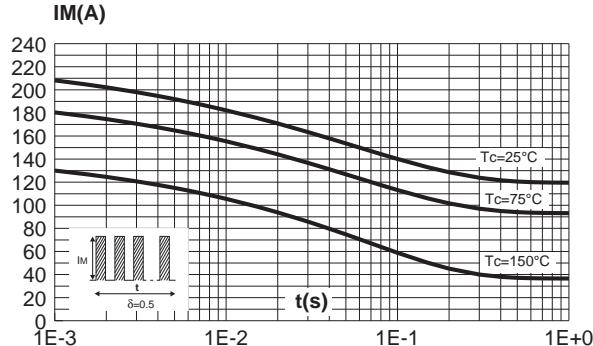


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

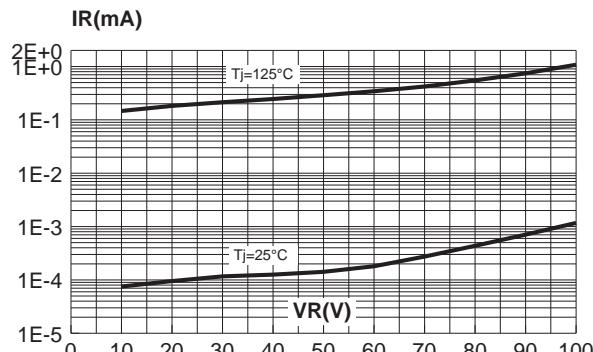


Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).

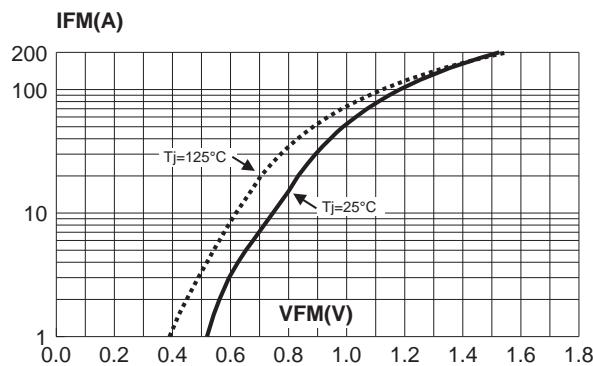


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

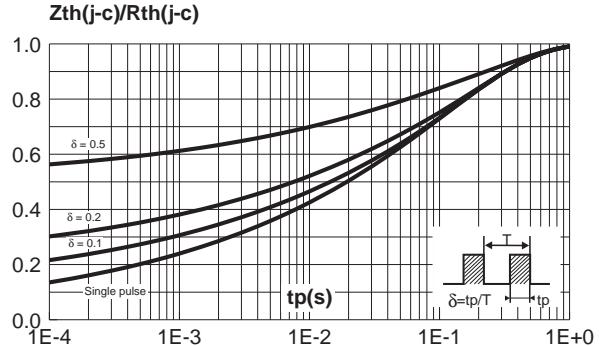
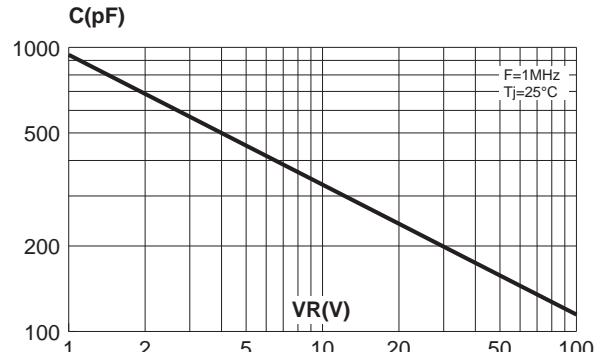
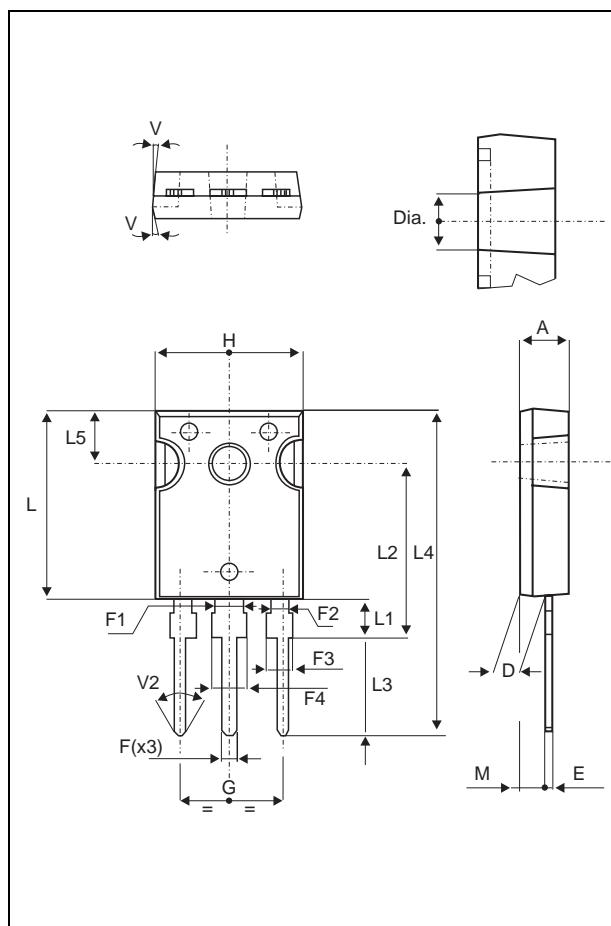


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).



STPS30H100CW

PACKAGE MECHANICAL DATA TO-247



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G	10.90				0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

- Cooling method: C
- Recommended torque value: 0.8 N.m.
- Maximum torque value: 1 N.m.

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS30H100CW	STPS30H100CW	TO-247	4.36g	30	Tube

- Epoxy meets UL94,V0

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